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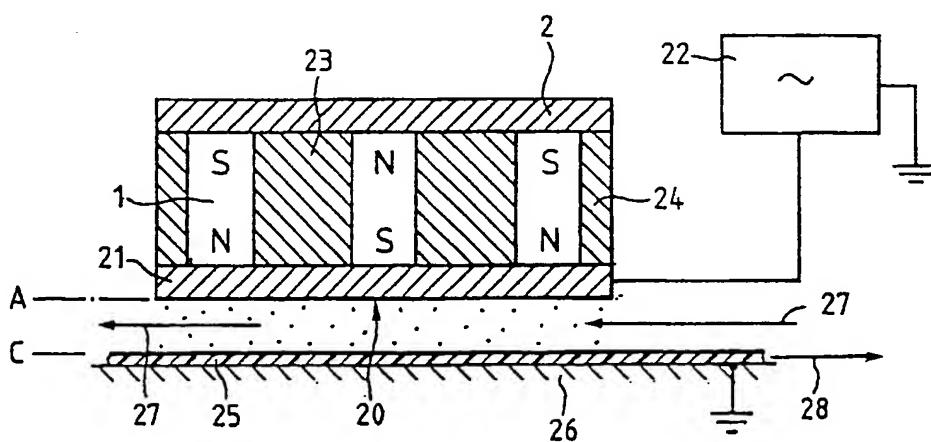
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(54) Title: DEVICE FOR CARRYING OUT A PLASMA-ASSISTED PROCESS

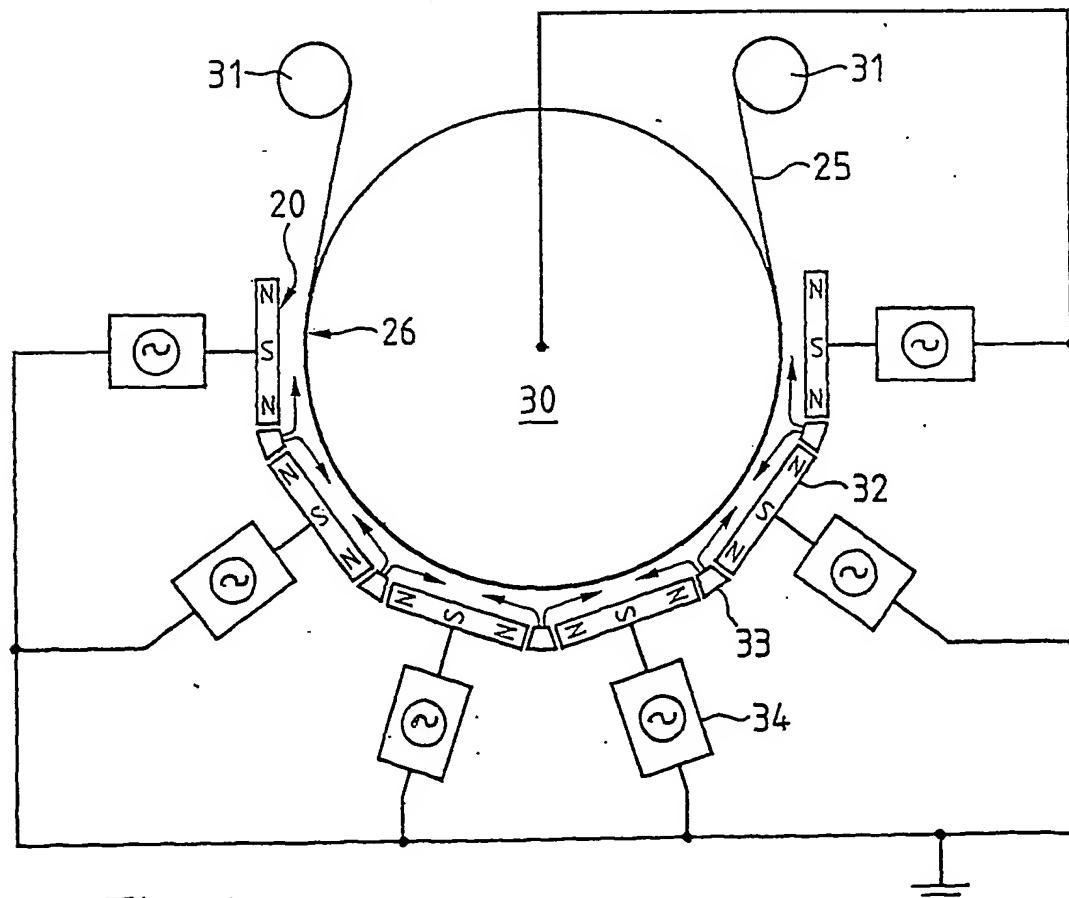
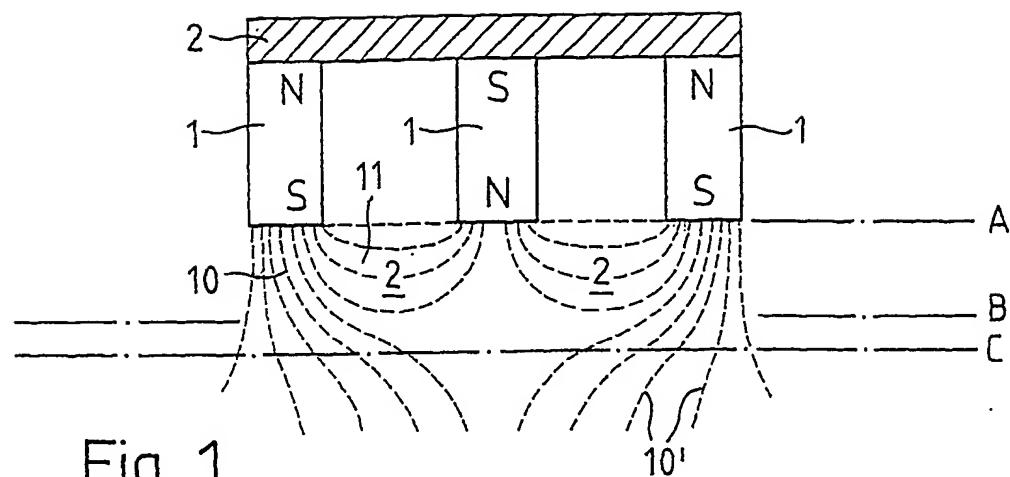
(54) Bezeichnung: VORRICHTUNG ZUR DURCHFÜHRUNG EINES PLASMA-UNTERSTÜTZTEN PROZESSES



(57) Abstract: Disclosed is a device for carrying out a plasma-assisted process, particularly plasma-assisted, chemical deposition from the gas phase. Said device comprises at least one unbalanced magnetron electrode which is disposed inside a vacuum chamber, is provided with a flat magnetron front (20) with peripheral and central magnet poles having opposite polarity, and is connected to a source (34) of AC voltage. Said device also comprises means for positioning a surface of a substrate (25), which is to be treated, so as to face the magnetron front, and a gas-feeding means for delivering a process gas or a process gas mixture into the intermediate space between the magnetron front (20) and the surface that is to be treated. In order to optimize the efficiency of the process (e.g. deposition rate), the distance between the magnetron front (20) and the surface that is to be treated is adapted to the magnetic field generated by the magnetron electrode (32) such that a bright plasma strip extends between darker tunnels which are formed by the lines of force extending from peripheral to central poles of the magnetron front and the surface that is to be treated. Said plasma strip has a minimal width while having a homogeneous brightness towards the surface that is to be treated. Preferably, the distance between the surface that is to be treated and the magnetron front is 2 to 20 percent greater than the height of the tunnel. The inventive device can be used for coating a plastic film with silicon oxide in order to improve the barrier properties of said film, for example.

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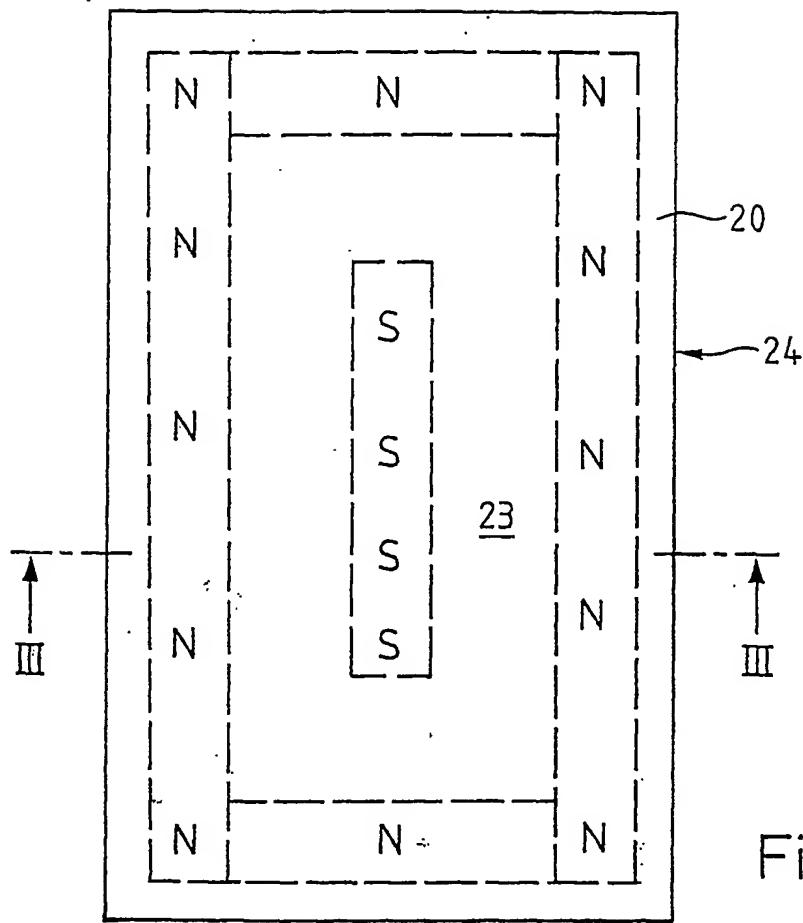


Fig. 2

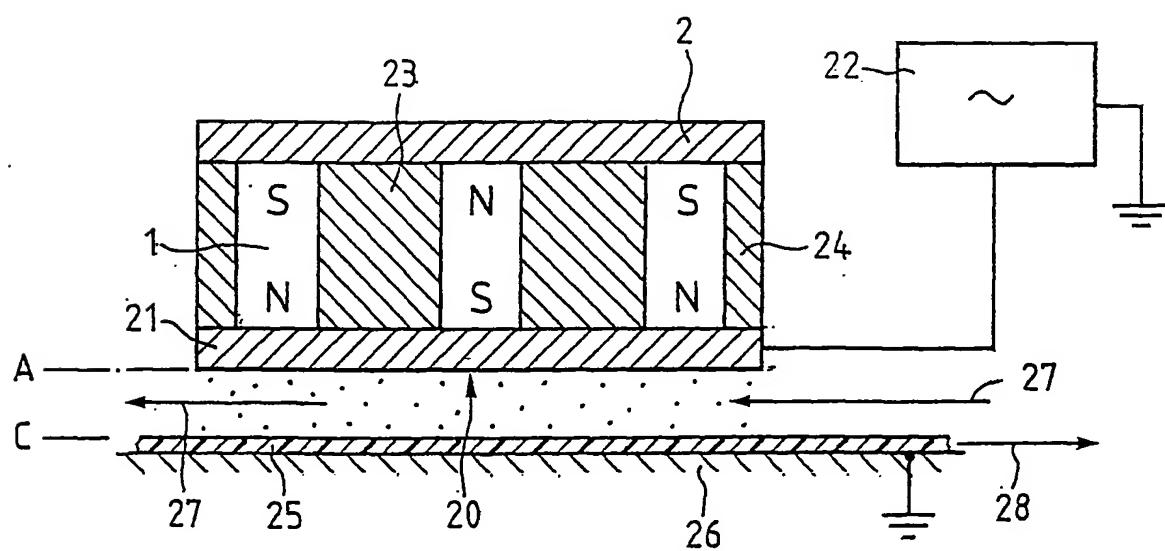


Fig. 3